and

at least one second sub-module disposed on the first sub-module, wherein the second sub-module comprises a second semiconductor switch, a second diode, a seventh electrode, an eighth electrode and a ninth electrode, wherein the second semiconductor switch comprises plural third conducting terminals, and the second diode comprises plural fourth conducting terminals, wherein the seventh electrode is electrically connected with the corresponding third conducting terminal of the second semiconductor switch and the corresponding fourth conducting terminal of the second diode, the eighth electrode is electrically connected with the corresponding third conducting terminal of the second semiconductor switch, and the ninth electrode is electrically connected with the corresponding third conducting terminal of the second semiconductor switch and the corresponding fourth conducting terminal of the second diode, wherein the seventh electrode is electrically connected with the upper sixth electrode of the first sub-module, the eighth electrode is electrically connected with the upper fifth electrode of the first sub-module, and the ninth electrode is electrically connected with the first electrode of the first sub-module.

2. The power module according to claim 1, wherein the first sub-module and the second sub-module are formed as a high-voltage-side switching element and a low-voltage-side switching element of a bridge circuit, respectively.

3. The power module according to claim 1 or 2, wherein the first semiconductor switch is an insulated-gate bipolar transistor, and the first semiconductor switch comprises three first conducting terminals, wherein the three first conducting terminals serve as a gate, an emitter and a collector, respectively, wherein the first electrode is electrically connected

with the emitter of the first semiconductor switch, the second electrode is electrically connected with the gate of the first semiconductor switch, and the third electrode is electrically connected with the collector of the first semiconductor switch.

4. The power module according to any of the preceding claims, wherein the first sub-module further comprises an auxiliary electrode, wherein the auxiliary electrode is located at the top side of the first sub-module, and arranged between the first electrode and the upper fifth electrode.

5. The power module according to claim 4, wherein the first sub-module further comprises a fixing material, wherein the fixing material is disposed on the auxiliary electrode, and the second sub-module is attached on the first sub-module through the fixing material.

6. The power module according to claim 4 or 5, wherein the first sub-module further comprises:

a first insulation layer, wherein plural first conductive vias and plural second conductive vias are formed in the first insulation layer;

a first conductive layer electroplated on a bottom surface of the first insulation layer, and divided into the second electrode, the third electrode, the fourth electrode, the lower fifth electrode and the lower sixth electrode; and

a second conductive layer electroplated on a top surface of the first insulation layer, and divided into the first electrode, the upper fifth electrodes, the upper sixth electrodes and the auxiliary electrode, wherein the first electrode and the auxiliary electrode are contacted with a first end of the corresponding first conductive via and a first end of the corresponding second conductive via, and the upper fifth electrodes and the upper sixth electrodes are contacted with the first end of the corresponding second conductive via.

7. The power module according to claim 6, wherein the first semiconductor switch and the first diode are embedded within the first insulation layer, wherein the first conducting terminal serving as the gate of the first semiconductor switch is contacted with a second end of the corresponding first conductive via so as to be electrically connected with the auxiliary electrode, the first conducting terminal serving as the emitter of the first semiconductor switch is contacted with the second end of the corresponding first conductive vias so as to be electrically connected with the first electrode, and the first conducting terminal serving as the collector of the first semiconductor switch is electrically connected with the third electrode, wherein the second conducting terminal serving as an anode of the first diode is contacted with the second end of the corresponding first conductive vias so as to be electrically connected with the first electrode, and the second conducting terminal serving as a cathode of the first diode is electrically connected with the third electrode.

8. The power module according to any of the preceding claims, wherein the first sub-module further comprises:

a first thermal conduction structure embedded within the first insulation layer, wherein the first thermal conduction structure is located near the first semiconductor switch and partially exposed outside the first insulation layer, so that the heat generated by the first semiconductor switch is transferred to the surroundings of the first sub-module through the first thermal conduction structure;

a second thermal conduction structure embedded within the first insulation layer, wherein the second thermal conduction structure is located near the first diode and partially exposed outside the first insulation layer, so that the heat generated by the first diode is transferred to the surroundings of the first sub-module through the second thermal

conduction structure;

a third thermal conduction structure embedded within the first insulation layer, wherein the third thermal conduction structure is located near the first thermal conduction structure and partially exposed outside the first insulation layer; and

a fourth thermal conduction structure embedded within the first insulation layer, wherein the fourth thermal conduction structure is located near the second thermal conduction structure and partially exposed outside the first insulation layer.

9. The power module according to claim 8, wherein the first thermal conduction structure, the second thermal conduction structure, the third thermal conduction structure and the fourth thermal conduction structure are made of metallic material, wherein the first thermal conduction structure is contacted with the second electrode and contacted with a second end of the corresponding second conductive via so as to be electrically connected with the auxiliary electrode, the second thermal conduction structure is contacted with the fourth electrode and contacted with the second end of the corresponding second conductive via so as to be electrically connected with the first electrode, the third thermal conduction structure is contacted with the lower fifth electrode and contacted with the second end of the corresponding second conductive via so as to be electrically connected with the upper fifth electrode, and the fourth thermal conduction structure is contacted with the lower sixth electrode and contacted with the second end of the corresponding second conductive via so as to be electrically connected with the upper sixth electrode.

10. The power module according to any of the preceding claims, wherein the second semiconductor switch is an insulated-gate bipolar transistor, and the second semiconductor switch comprises three third conducting

terminals, wherein the three third conducting terminals serve as a gate, an emitter and a collector, respectively, wherein the seventh electrode is electrically connected with the emitter of the second semiconductor switch, the eighth electrode is electrically connected with the gate of the second semiconductor switch, and the ninth electrode is electrically connected with the collector of the second semiconductor switch.

11. The power module according to any of the preceding claims, wherein the second sub-module further comprises:

a second insulation layer, wherein plural third conductive vias and plural fourth conductive vias are formed in the second insulation layer;

a third conductive layer electroplated on a bottom surface of the second insulation layer, and divided into the seventh electrode, the eighth electrode and the ninth electrode;

a fourth conductive layer electroplated on a top surface of the second insulation layer, and divided into a first conductive block and a second conductive block, wherein the first conductive block and the second conductive block are contacted with a first end of the corresponding third conductive via and a first end of the corresponding fourth conductive via;

a third insulation layer disposed on the fourth conductive layer; and

a fifth conductive layer electroplated on the third insulation layer.

12. The power module according to claim 11, wherein the second semiconductor switch and the second diode are embedded within the second insulation layer, wherein the third conducting terminal serving as the gate of the second semiconductor switch is contacted with a second end of the corresponding third conductive via so as to be electrically connected with the second conductive block, the third conducting terminal serving as the emitter of the second semiconductor switch is contacted with the second end of the corresponding third conductive via so as to be

electrically connected with the first conductive block, and the third conducting terminal serving as the collector of the second semiconductor switch is disposed on and contacted with the ninth electrode, wherein the fourth conducting terminal serving as an anode of the second diode is contacted with the second end of the corresponding third conductive via so as to be electrically connected with the first conductive block, and the fourth conducting terminal serving as a cathode of the second diode is disposed on and contacted with the ninth electrode.

13. The power module according to claim 11 or 12, wherein the second sub-module further comprises:

a fifth thermal conduction structure embedded within the second insulation layer, wherein the fifth thermal conduction structure is located near the second semiconductor switch and partially exposed outside the second insulation layer, so that the heat generated by the second semiconductor switch is transferred to the surroundings of the second sub-module through the fifth thermal conduction structure; and

a sixth thermal conduction structure embedded within the second insulation layer, wherein the sixth thermal conduction structure is located near the second diode and partially exposed outside the second insulation layer, so that the heat generated by the second diode is transferred to the surroundings of the second sub-module through the sixth thermal conduction structure.

14. The power module according to claim 13, wherein the fifth thermal conduction structure and the sixth thermal conduction structure are made of metallic material, wherein the fifth thermal conduction structure is contacted with the eighth electrode and contacted with a second end of the corresponding fourth conductive via so as to be electrically connected with the second conductive block, and the sixth thermal conduction structure is

contacted with the seventh electrode and contacted with the second end of the corresponding fourth conductive via so as to be electrically connected with the first conductive block.

15. The power module according to any of the preceding claims, further comprising a first heat dissipation device and/or a second heat dissipation device, wherein the first heat dissipation device is contacted with the second sub-module, and the second heat dissipation device is contacted with the substrate.